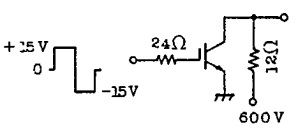


TOSHIBA SEMICONDUCTOR
TECHNICAL DATA

MG50N2YS1

ELECTRICAL CHARACTERISTICS (Ta=25°C)

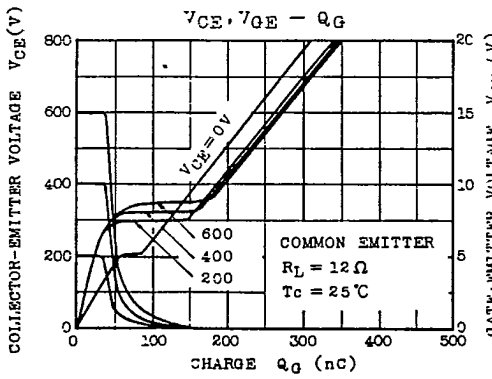
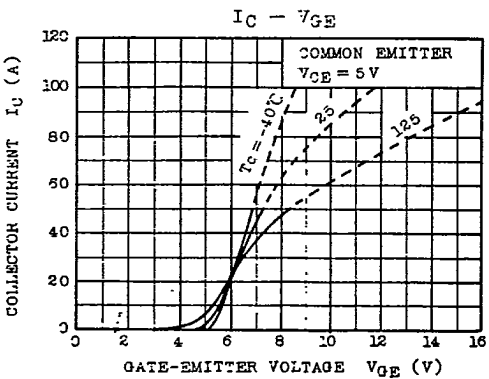
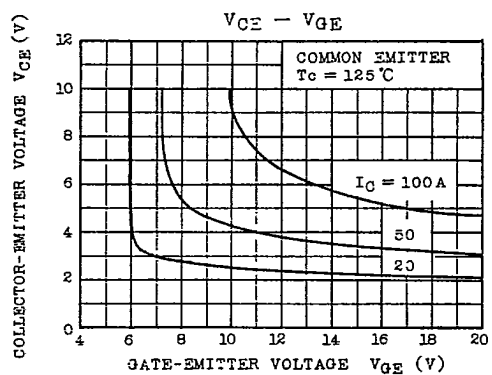
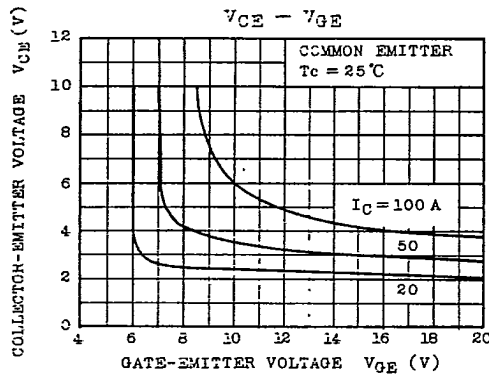
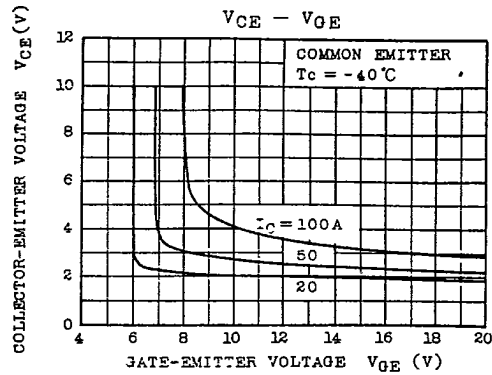
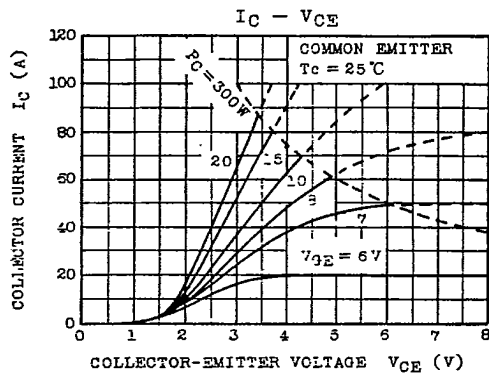
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		IGES	VGE=±20V, VCE=0	-	-	±500	nA
Collector Cut-off Current		ICES	VCE=1000V, VGE=0	-	-	1.0	mA
Collector-Emitter Breakdown Voltage		V(BR)CES	IC=2mA, VGE=0	1000	-	-	V
Gate-Emitter Cut-off Voltage		VGE(OFF)	IC=50mA, VCE=5V	3.0	-	6.0	V
Collector-Emitter Saturation Voltage		VCE(sat)	IC=50A, VGE=15V	-	3.0	5.0	V
Input Capacitance		Cies	VCE=10V, VGE=0, f=1MHz	-	7200	-	pF
Switching Time	Rise Time	tr		-	0.35	1.0	μs
	Turn-on Time	ton		-	0.45	1.0	
	Fall Time	tf		-	0.6	1.0	
	Turn-off Time	toff		-	1.1	1.5	
Forward Voltage		VF	IF=50A, VGE=0	-	2.0	2.5	V
Reverse Recovery Time		trr	IF=50A, VGE=-10V di/dt=100A/μs	-	0.25	0.5	μs
Thermal Resistance		Rth(j-c)	Transistor	-	-	0.41	°C/W
			Diode	-	-	1.0	

ECA-MG50N2YS1-2

TOSHIBA CORPORATION

TOSHIBA SEMICONDUCTOR
TECHNICAL DATA

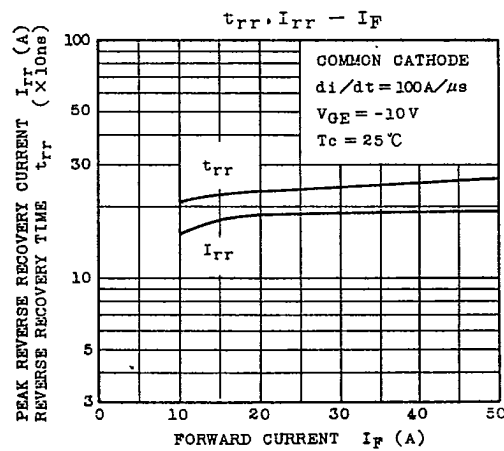
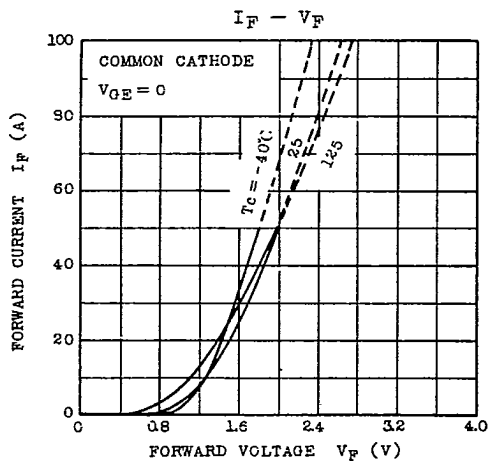
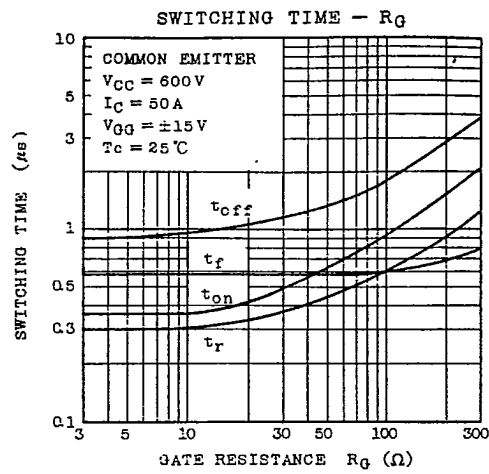
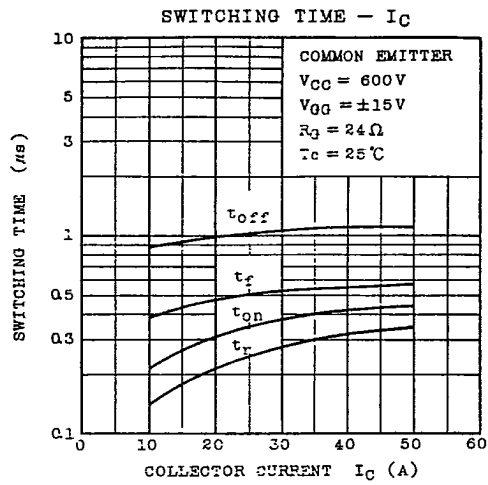
MG50N2YS1



EGA-MG50N2YS1-3
TOSHIBA CORPORATION

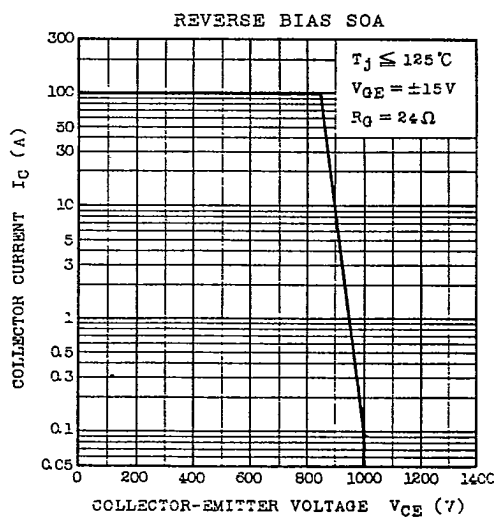
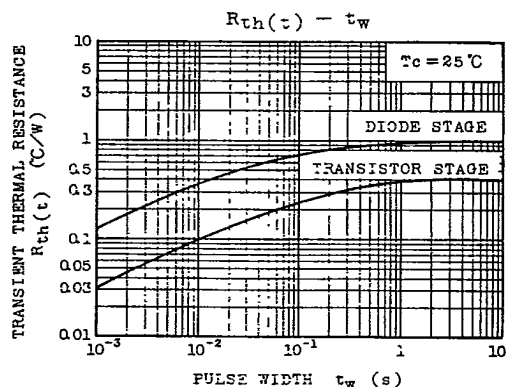
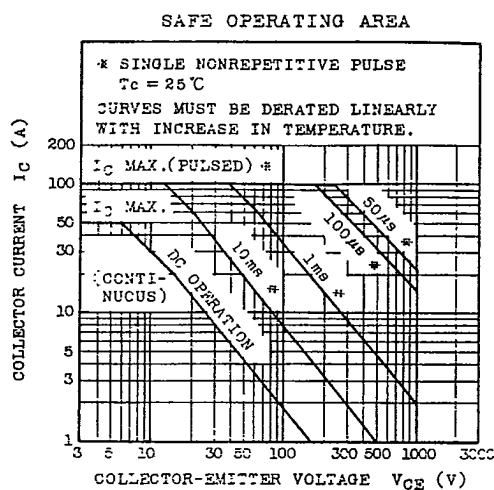
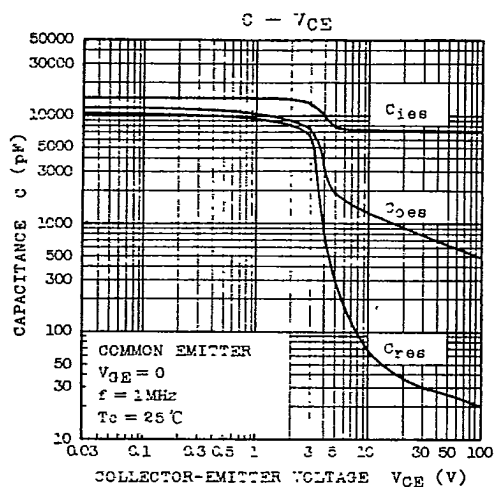
TOSHIBA SEMICONDUCTOR
TECHNICAL DATA

MG50N2YS1



TOSHIBA SEMICONDUCTOR
TECHNICAL DATA

MG50N2YS1



EGA-MG50N2YS1-5
TOSHIBA CORPORATION